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## Patent Abstracts of Japan

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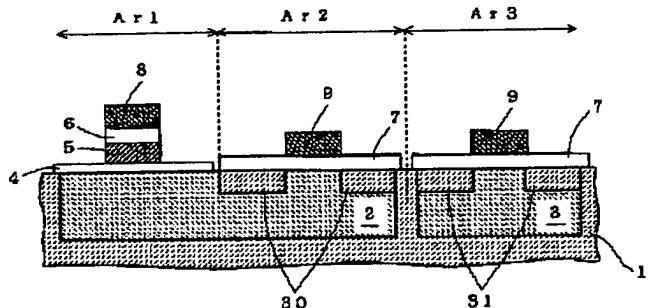
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APPLICANT : MITSUBISHI ELECTRIC CORP;

INVENTOR : SAKAKIBARA KIYOHICO;

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TITLE : MANUFACTURE OF NON-VOLATILE  
 SEMICONDUCTOR STORAGE DEVICE



**ABSTRACT** : PURPOSE: To dispense with a process for forming a peripheral transistor by a method wherein the source.drain of a second MOS transistor is formed using a floating gate formed on a semiconductor region, which contains a region where the source.drain of a first MOS transistor is formed, as a mask.

CONSTITUTION: A floating gate 5 is formed on a semiconductor region, which includes an N region where a P-region that forms the source.drain region of a P-channel MOS transistor is formed, using an ONO film 6 as a mask, wherein the ONO film 6 is etched through a control gate 8 as a mask. Then, the control gate 8 and the gate 9 of cells are patterned using the floating gate 5 as a mask, and then N-type impurities are injected into all the surface of a substrate for the formation of an N' region. At this point, the N' region is formed with the gates 9 of an N-channel MOS transistor and a P-channel MOS transistor as a mask.

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